Remarks

This amendment is further to the amendment mailed on or about September 30, 2005. The claimed invention operates in IGBTs and in MOSFETs. An IGBT has collector and emitter terminals highly doped with dopants of opposite polarity and a MOSFET has source and drain terminals highly doped with dopants of the same polarity. The claims as amended now read on both types of devices and any inconsistency between the broad claims and the detailed claims to the MOSFET (e.g. claims 29, 30, 31, 42) are eliminated.

Respectfully submitted,

HISCOCK & BARCLAY, LLP

By: _____

Thomas R. FitzGerald
Reg. No. 26,730
2000 HSBC Plaza
Rochester, NY 14604
Tel: (585) 325-7570
Fax: (585) 325-5458